Silicon P-Channel MOS FET

HITACHI

Application

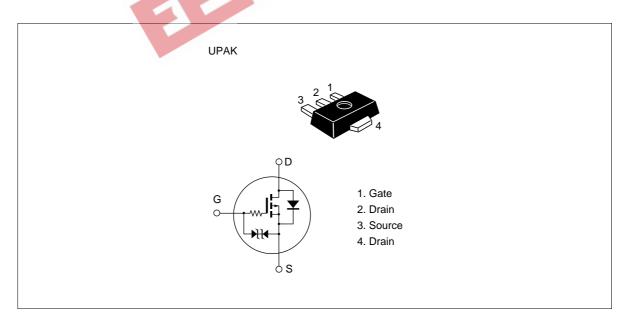
High speed power switching

Low voltage operation

Features

- Very low on-resistance
- High speed switching
- Suitable for camera or VTR motor drive circuit, power switch, solenoid drive and etc.

Outline





Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

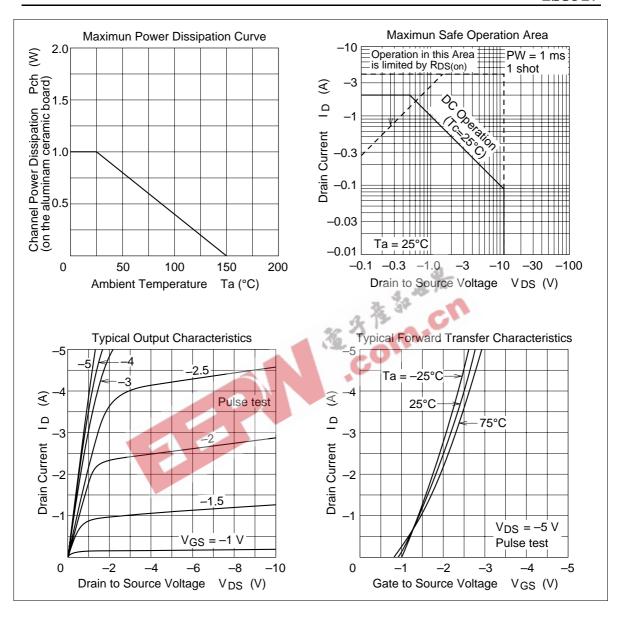
Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{ exttt{DSS}}$	-12	V
Gate to source voltage	V_{GSS}	-7	V
Drain current	I _D	±2	Α
Drain peak current	l _{D(pulse)} *1	±4	А
Body to drain diode reverse drain current	I _{DR}	2	А
Channel dissipation	Pch*2	1	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

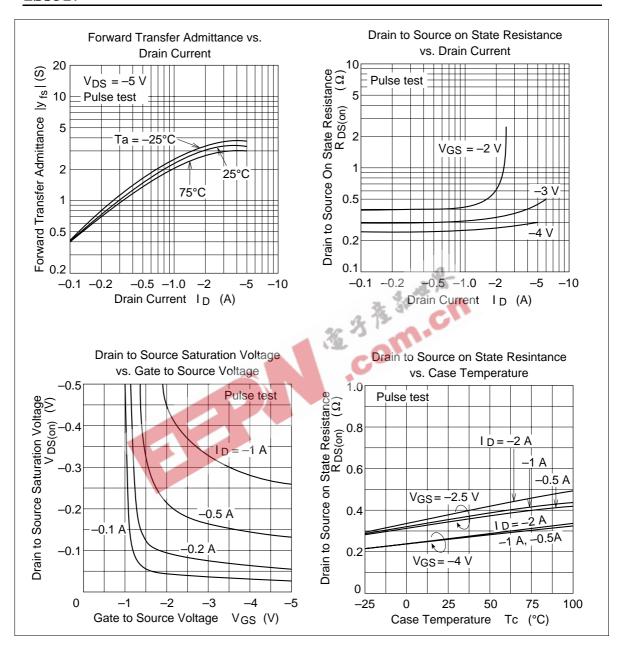
- 2. Value on the alumina ceramic board (12.5×20×0.7 mm).
- 3. Marking is "NY".

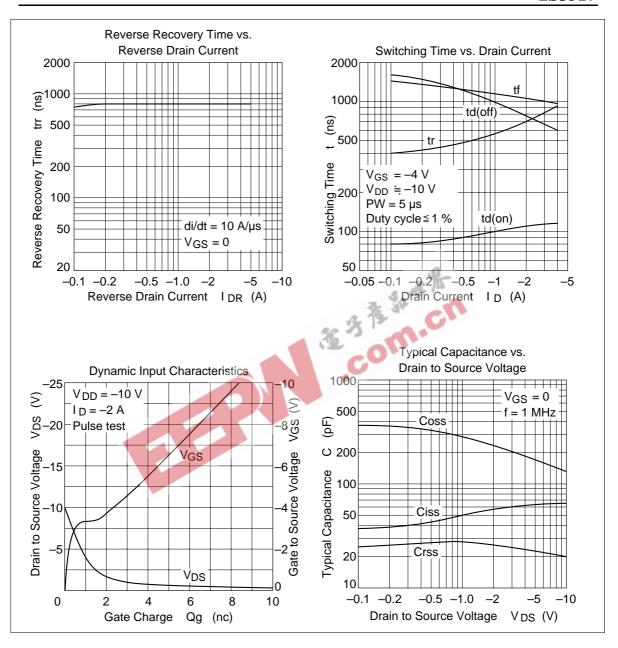
Electrical Characteristics (Ta = 25°C)

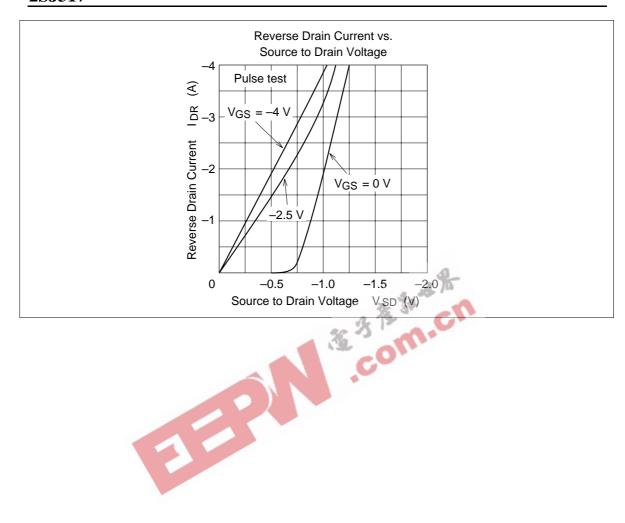
Notes: 1. PW \leq 100 μ s, duty cycle \leq 10%								
2. Value on the alumina ceramic board (12.5×20×0.7 mm).								
3. Marking is "NY".								
			0.0	头门				
2. Value on the alumina ceramic board (12.5×20×0.7 mm). 3. Marking is "NY". Electrical Characteristics (Ta = 25°C)								
Item	Symbol	Min	Тур	Max	Unit	Test conditions		
Drain to source breakdown voltage	V _{(BR)DSS}	-12	-	_	V	$I_D = -1 \text{ mA}, V_{GS} = 0$		
Gate to source breakdown voltage	V _{(BR)GSS}	±7	_	_	V	$I_{\text{G}}=\pm 10~\mu\text{A},~V_{\text{DS}}=0$		
Gate to source cutoff current	I _{GSS}	_	_	±5	μΑ	$V_{GS} = \pm 6.5 \text{ V}, V_{DS} = 0$		
Zero gate voltage drain current	I _{DSS}	_	_	– 1	μΑ	$V_{DS} = -8 \text{ V}, V_{GS} = 0$		
Gate to source cutoff voltage	$V_{\text{GS(off)}}$	-0.4	_	-1.4	V	$I_D = -100 \mu A, V_{DS} = -5 V$		
Static drain to source on state	$R_{\scriptscriptstyle DS(on)1}$	_	0.4	0.7	Ω	$I_D = -0.5 \text{ A}^{*1}, V_{GS} = -2.2 \text{ V}$		
resistance	$R_{\scriptscriptstyle DS(on)2}$	_	0.28	0.35	Ω	$I_D = -1 A^{*1}, V_{GS} = -4 V$		
Forward transfer admittance	$ y_{fs} $	1.0	2.3	_	S	$I_D = -1 A^{*1}, V_{DS} = -5 V$		
Input capacitance	Ciss	_	63	_	pF	$V_{DS} = -5 \text{ V}, V_{GS} = 0,$		
Output capacitance	Coss	_	180	_	pF	f = 1 MHz		
Reverse transfer capacitance	Crss	_	23	_	pF			
Turn-on time	t _{on}	_	500	_	ns	$I_D = -0.2 \text{ A}^{*1}, \text{ Vin} = -4 \text{ V},$		
Turn-off time	t _{off}	_	2860	_	ns	$R_L = 51 \Omega$		

Note: 1. Pulse test



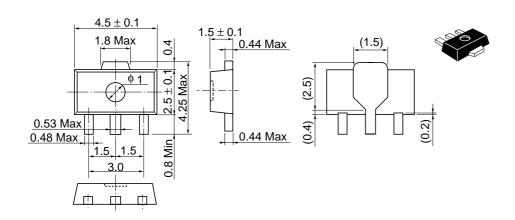








Unit: mm



Hitachi Code	UPAK
JEDEC	_
EIAJ	Conforms
Weight (reference value)	0.050 g

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